



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 30V
- I_D 3.6A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 33mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) 48mohm
- 100% V_{DS} Tested

General Description

- Trench Power MV MOSFET technology
- High Power and current handing capability
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- PWM application
- Load switch

■ Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
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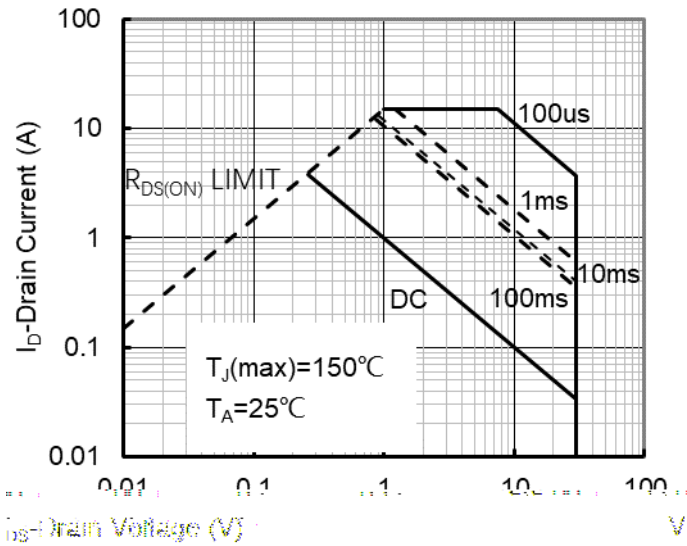


Figure7. Safe Operation Area

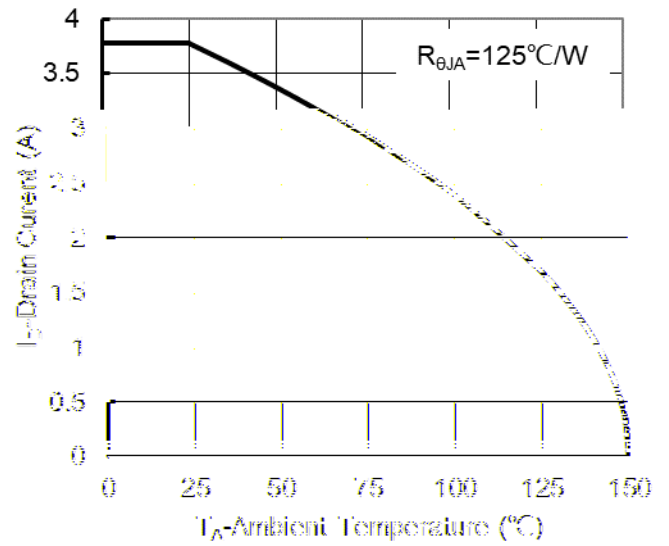
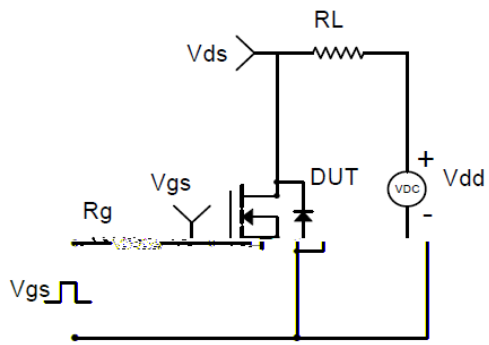


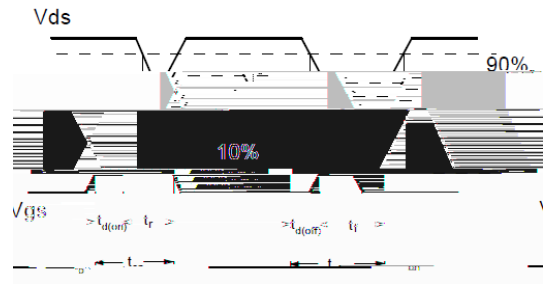
Figure8. Maximum Continuous Drain Current vs Ambient Temperature



Figure9. Normalized Maximum Transient Thermal Impedance

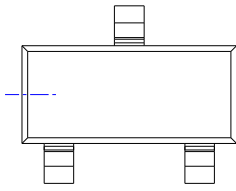


Resistive





■ SOT-23 Package information



UNIT mm



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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, etc.).